New Product

Vishay Siliconix

Quad SPST CMOS Analog Switch with Latches

FEATURES

BENEFITS

APPLICATIONS

- Accepts 150-ns Write Pulse Width
- 5-V On-Chip Regulator
- Latches Are Transparent with WR Low
- Low On-Resistance: 60 Ω
- Compatible with Most μP Buses
- Allows Wide Power Supply Tolerance Without Affecting TTL Compatibility
- Reduced Power Consumption
- Allows Flexibility of Design
- μP Based Systems
- Automatic Test Equipment
- Communication Systems
- Data Acquisition Systems
- Medical Instrumentation
- Factory Automation

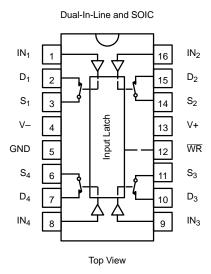
DESCRIPTION

The DG221B is a monolithic quad single-pole, single-throw analog switch designed for precision switching applications in communication, instrumentation and process control systems. Featuring independent onboard latches and a common $\overline{\text{WR}}$ pin, each DG221B can be memory mapped, and addressed as a single data byte for simultaneous switching.

The DG221B combines low power and low on-resistance (60 Ω typical) while handling continuous currents up to 20 mA. An epitaxial layer prevents latchup.

The device features true bidirectional performance in the on condition.

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Four Latchable SPST Switches per Package

TRUTH TABLE					
IN _X WR Switch					
0	0	ON			
1	0	OFF			
х	Ŀ	Control data latched-in, switches on or off as selected by last IN _X			
Х	1	Maintains previous state			

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

ORDERING INFORMATION					
Temp Range	Package	Part Number			
-40°C to 85°C	16-Pin Plastic DIP	DG221BDJ			
-40 C t0 65 C	16-Pin Narrow SOIC	DG221BDY			

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ABSOLUTE MAXIMUM RATINGS

Voltages Referenced to V-	
V+	34 \
GND	
Digital Inputs ^a , V _S , V _D	(V-) -2 V to (V+) +2 \
or 20 mA	, whichever occurs firs
Continuous Current (Any Terminal)	30 mA
Continuous Current, S or D	20 m/
Peak Current S or D (Pulsed 1 ms. 10% duty cycle)	70 m/

Storage Temperature:	(DJ and DY Suffix)65	to 125°C
Power Dissipation (Package	e) ^b	
16-Pin Plastic DIPc		470 mW
16-Pin SOIC ^d		600 mW

- a. Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
 b. All leads welded or soldered to PC Board.
 c. Derate 6.5 mW/°C above 25°C
 d. Derate 7.7 mW/°C above 75°C

SCHEMATIC DIAGRAM (TYPICAL CHANNEL)

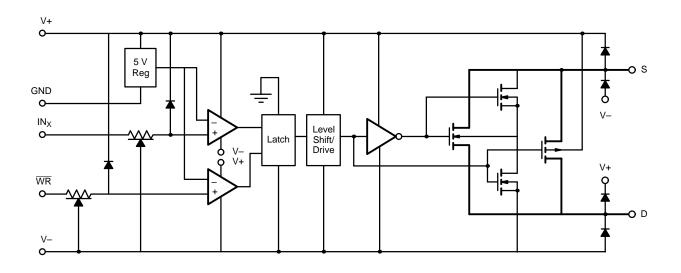


FIGURE 1.



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SPECIFICATIONS	3						
		Test Conditions Unless Otherwise Specified		Limits -40 to 85°C			
Parameter	Symbol	V+ = 15 V, V- = -15 V $V_{IN} = 2.4 \text{ V}, 0.8^{f} \text{ V}, \overline{\text{WR}} = 0$	Temp ^b	Mind	Турс	Max ^d	Unit
Analog Switch			1	•		'	
Analog Signal Rangee	V _{ANALOG}		Full	-15		15	V
Drain-Source On-Resistance	r _{DS(on)}	$I_S = -10$ mA, $V_D = \pm 10$ V	Room Full		60	90 135	Ω
Source Off Leakage Current	I _{S(off)}		Room Full	-5 -100	±0.01	5 100	
Drain Off Leakage Current	I _{D(off)}	$V_S = \pm 14 \text{ V}, V_D = \mp 14 \text{ V}$	Room Full	-5 -100	±0.02	5 100	nA
Drain On Leakage Current	I _{D(on)}	$V_S = V_D = \pm 14 \text{ V}$	Room Full	-5 -200	±0.01	5 200	
Digital Control	1		1		•	· I	
Input Current I _{INL} , I _{INH}		V _{IN} = 0 V or = 2.4 V	Room Full	-1 -10	-0.0004	1 10	μΑ
Dynamic Characteristic	cs		1				
Turn-On Time	t _{ON}	0 5:	Room			550	
Turn-Off Time	t _{OFF}	See Figure 2	Room			340	
Turn-On Time Write	t _{ON} , WR	0 5: 0	Room			550	
Turn-Off Time Write	t _{OFF} , WR	See Figure 3	Room			340	ns
Write Pulse Width	t _W		Room	150	120		
Input Setup Time	ts	See Figure 4	Room	180	130		
Input Hold Time	t _H		Room	20	18		
Charge Injection	Q	$C_L = 1000 \text{ pF}$ $V_{GEN} = 0 \text{ V}, R_{GEN} = 0 \Omega$	Room		20		pC
Source-Off Capacitance	C _{S(off)}		Room		8		
Drain-Off Capacitance	C _{D(off)}	$f = 1 \text{ MHz}, V_S, V_D = 0 \text{ V}$	Room		9		pF
Channel-On Capacitance	C _{D(on)}		Room		29		
Off Isolation	OIRR	Ve = 1 Vo n f = 100 kHz	Room		70		
Interchannel Crosstalk	X _{TALK}	$V_S = 1 V_{p-p}$, $f = 100 \text{ kHz}$ $C_L = 15 \text{ pF}$, $R_L = 1 \text{ k}\Omega$	Room		90		dB
Power Supplies	'		•				
Positive Supply Current	I+	All Channels On or Off	Full		0.8	1.5	
Negative Supply Current	I–	V _{IN} = 0 V or 2.4 V	Room	-1	-0.4		mA

Notes:

- tes:

 Refer to PROCESS OPTION FLOWCHART.

 Room = 25°C, Full = as determined by the operating temperature suffix.

 Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

 The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

 Guaranteed by design, not subject to production test.

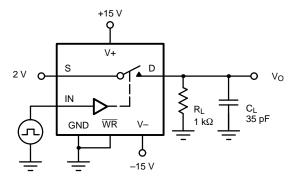
 V_{IN} = input voltage to perform proper function.

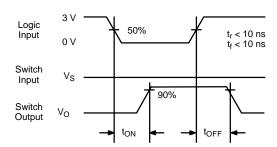
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TEST CIRCUITS



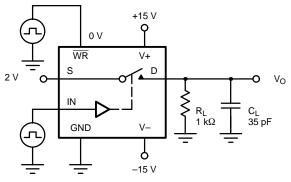


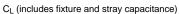
C_L (includes fixture and stray capacitance)

$$V_O = V_S$$

$$\frac{R_L}{R_L + r_{DS(on)}}$$

FIGURE 2. Switching Time





$$V_{O} = V_{S} \qquad \frac{R_{L}}{R_{L} + r_{DS(on)}}$$

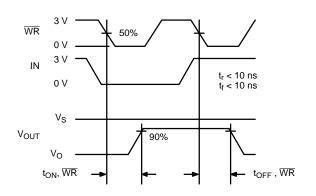
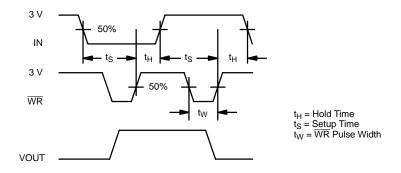


FIGURE 3. WR Switching Time



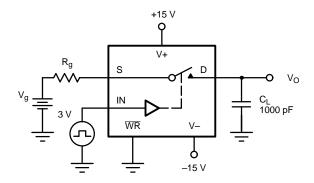
The latches are level sensitive. When \overline{WR} is held low the latches are transparent and the switches respond to the digital inputs. The digital inputs are latched on the rising edge of \overline{WR} .

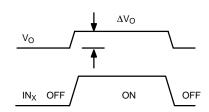
FIGURE 4. WR Setup Conditions

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TEST CIRCUITS





 ΔV_O = measured voltage error due to charge injection The charge injection in coulombs is Q = C_L x ΔV_O

FIGURE 5. Charge Injection

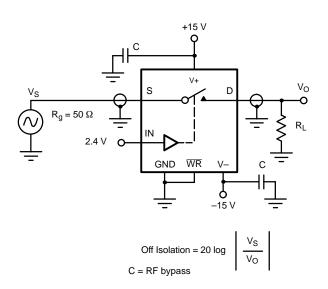


FIGURE 6. Off Isolation

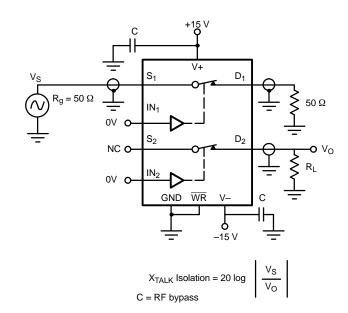


FIGURE 7. Channel-to-Channel Crosstalk

APPLICATION HINTS ^a							
V+ V- Positive Supply Voltage (V) Voltage (V) (V)		GND (V)			V _S or V _D Analog Voltage Range (V)		
15	-15	0	2.4/0.8	2.4/0.8	-15 to 15		
10	-10	0	2.4/0.8	2.4/0.8	-10 to 10		
10	-5	0	2.4/0.8	2.4/0.8	-5 to 10		

Notes:

a. Application Hints are for DESIGN AID ONLY, not guaranteed and not subject to production testing.



APPLICATIONS

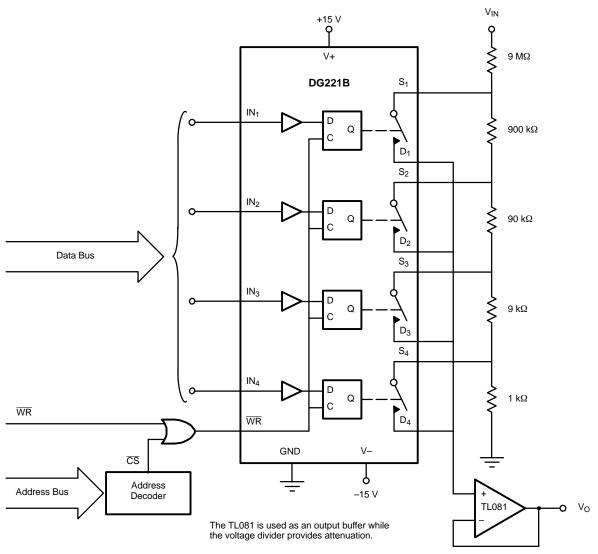


FIGURE 8. μP-Controlled Analog Signal Attenuator

TRUTH TABLE						
IN ₁	IN ₂	IN ₃	IN ₄	WRA	ON SWITCH	
0	0	0	0	0	All	
1	1	1	1	0	None	
0	1	1	1	0	1	
1	0	1	1	0	2	
1	1	0	1	0	3	
1	1	1	0	0	4	

OUTI	OUTPUT ATTENUATION FOR FIGURE 8						
WR	IN ₁	IN ₂	IN ₃	IN ₄	Gain		
0	0	1	1	1	0.1		
0	1	0	1	1	0.01		
0	1	1	0	1	0.001		
0	1	1	1	0	0.0001		

Notes: a. \overline{WR} may be held at "0" for temporary operation similar to DG201A/DG201B. With \overline{WR} at "0" SW₁ will remain on as long as IN₁ is held at "0".



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